

2SA1084, 2SA1085

Silicon PNP Epitaxial

REJ03G0635-0300
(Previous ADE-208-1007A)

Rev.3.00

Aug.10.2005

Application

Low frequency low noise amplifier

Outline

RENESAS Package code: PRSS0003DA-A
(Package name: TO-92 (1))

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1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	2SA1084	2SA1085	Unit
Collector to base voltage	V_{CBO}	-90	-120	V
Collector to emitter voltage	V_{CEO}	-90	-120	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-100	-100	mA
Emitter current	I_E	100	100	mA
Collector power dissipation	P_C	400	400	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

Electrical Characteristics

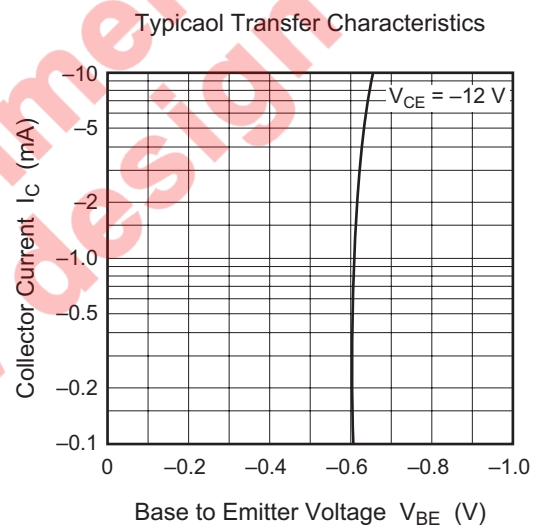
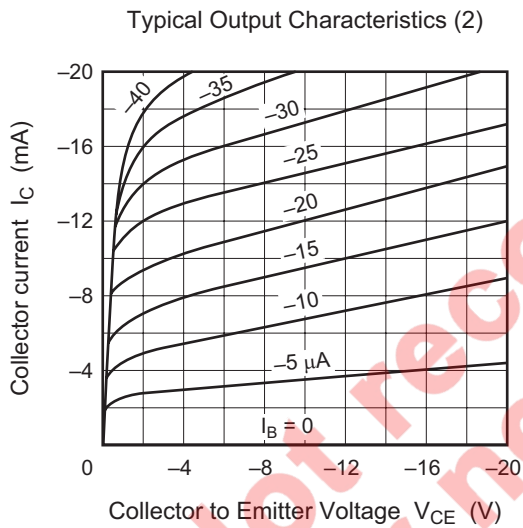
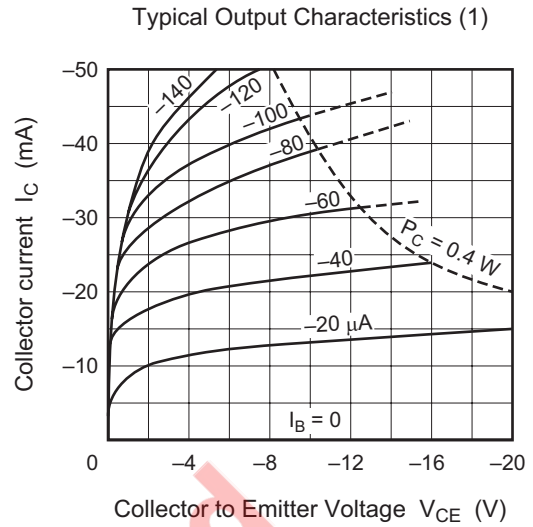
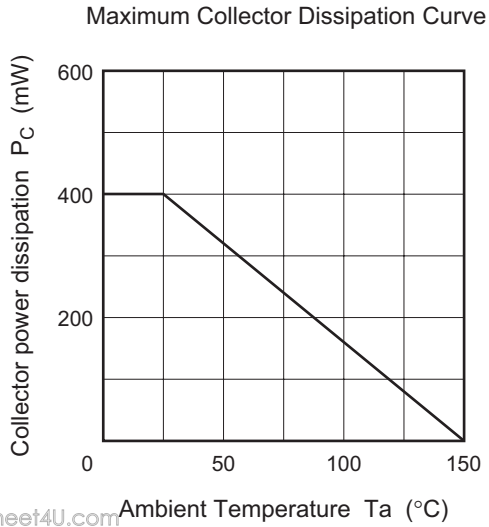
(Ta = 25°C)

Item	Symbol	2SA1084			2SA1085			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-90	—	—	-120	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	—	—	-120	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.1	—	—	-0.1	μA	$V_{CB} = -50 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.1	—	—	-0.1	μA	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800	250	—	800		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.2	—	—	-0.2	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$
Base to emitter voltage	V_{BE}	—	-0.6	—	—	-0.6	—	V	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Gain bandwidth product	f_T	—	90	—	—	90	—	MHz	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector output capacitance	C_{ob}	—	3.5	—	—	3.5	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Noise voltage referred to input	e_n	—	0.5	—	—	0.5	—	nV/ $\sqrt{\text{Hz}}$	$V_{CE} = -6 \text{ V}, I_C = -10 \text{ mA}, f = 1 \text{ kHz}, R_g = 0, \Delta f = 1 \text{ Hz}$

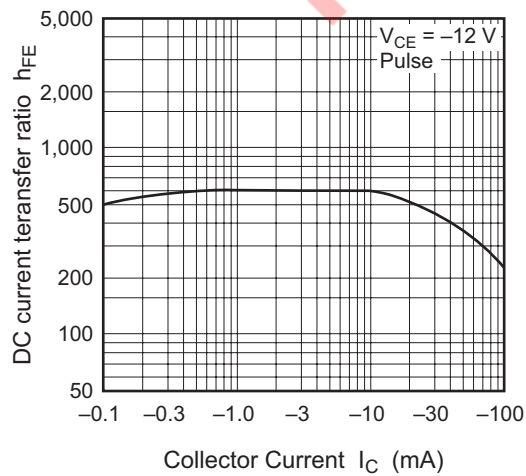
Note: 1. The 2SA1084 and 2SA1085 are grouped by h_{FE} as follows.

D	E
250 to 500	400 to 800

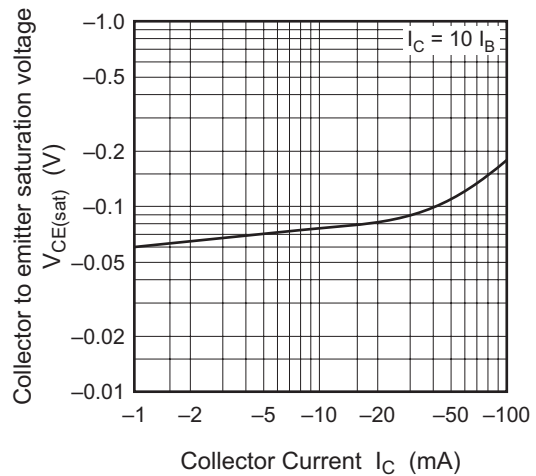
Main Characteristics

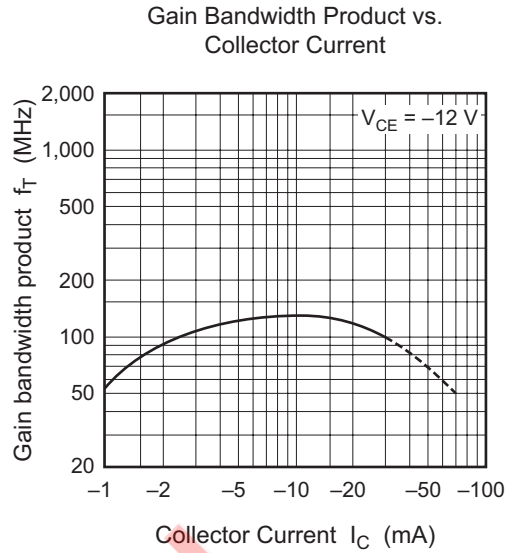
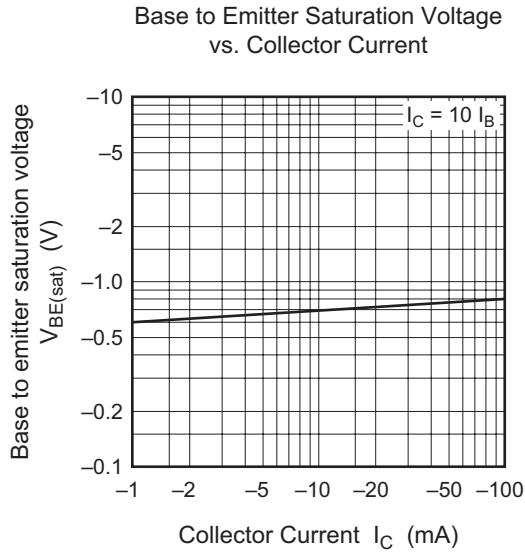


DC Current Transfer Ratio vs. Collector Current

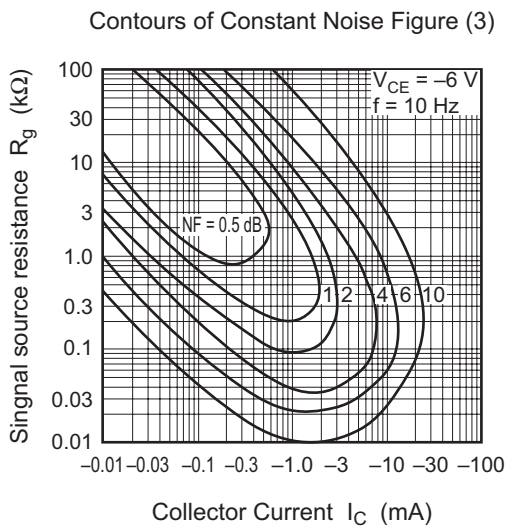
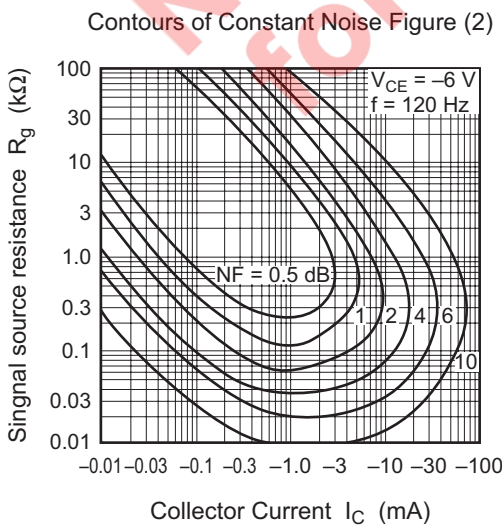
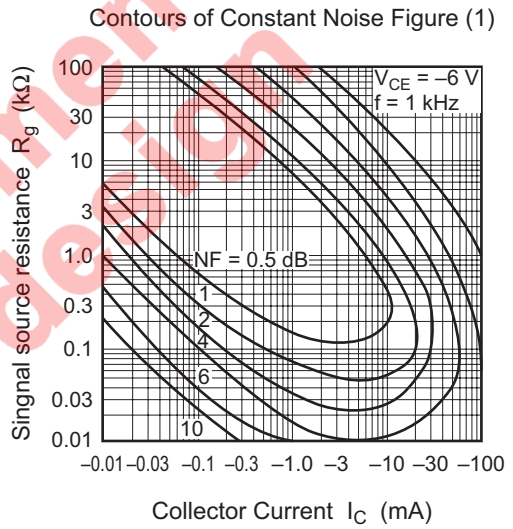
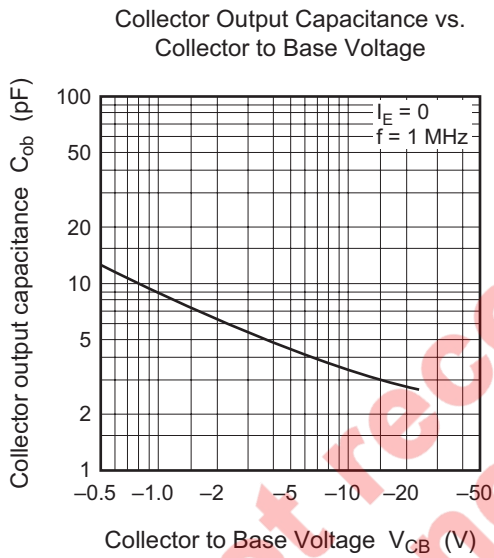


Collector to Emitter Saturation Voltage vs. Collector Current

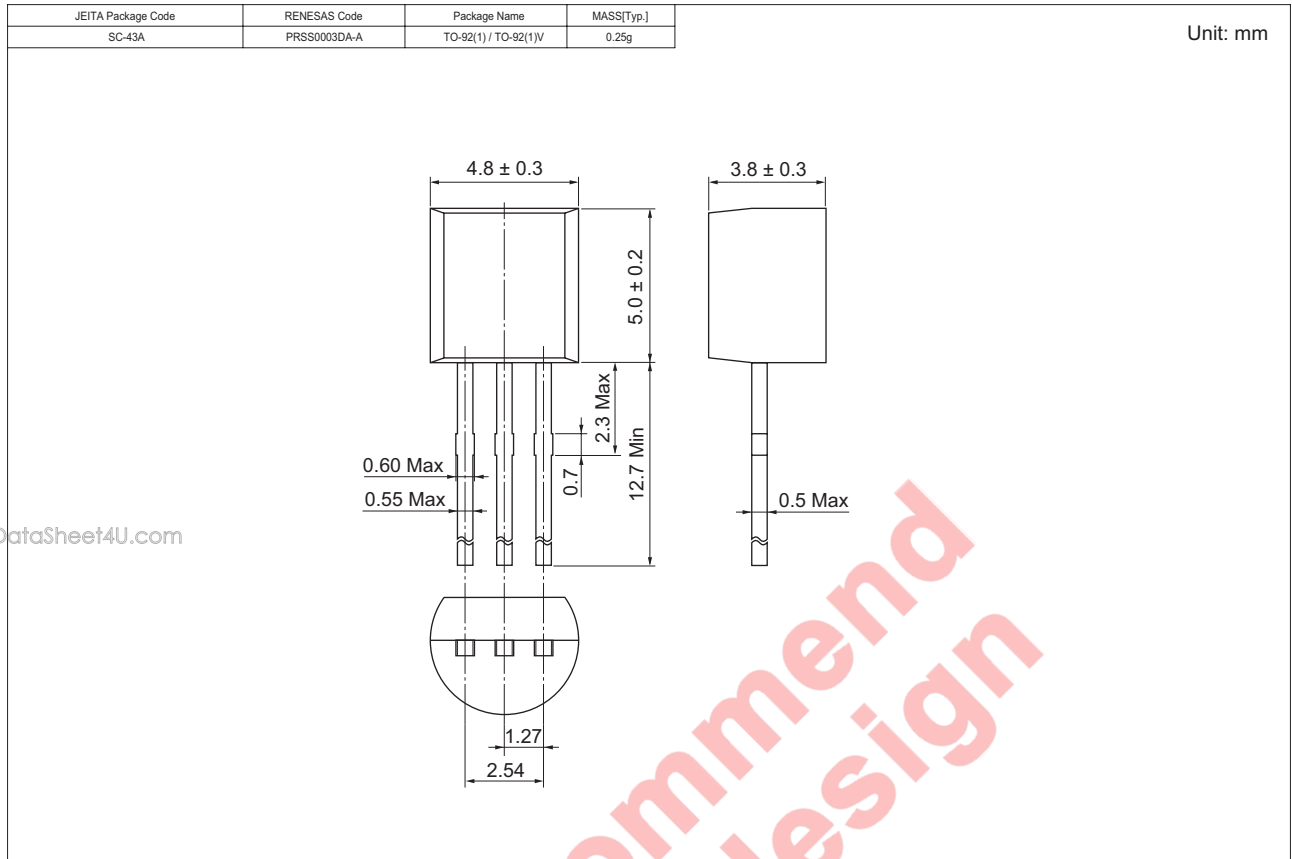




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Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SA1084ETZ-E 2SA1085DTZ-E 2SA1085ETZ-E	2500	Hold Box, Radial Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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